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1 ABSTRACT OF THE DISCLOSURE

 A fabrication method of a semiconductor
device is disclosed. The method includes the following
steps. First, a given number of projection electrodes
5 are formed on each of a given number of semiconductor
chips, and a thermosetting insulating adhesive is
applied to areas of mounting parts where the
semiconductor chips are to be mounted on a substrate.
Second, the thermosetting insulating adhesive on the
10 substrate is heated with a half-thermosetting
temperature. Third, the semiconductor chips are
aligned to the mounting parts of the substrate and a
first fixing of the semiconductor chips is performed
with a first pressure. Fourth, the substrate, on which
15 the semiconductor chips are fixed, is heated with a
thermosetting temperature of the thermosetting
insulating adhesive, and a second fixing of the
semiconductor chips is performed with a second
pressure.